

# Infrared Emitting Diode

Module No.:

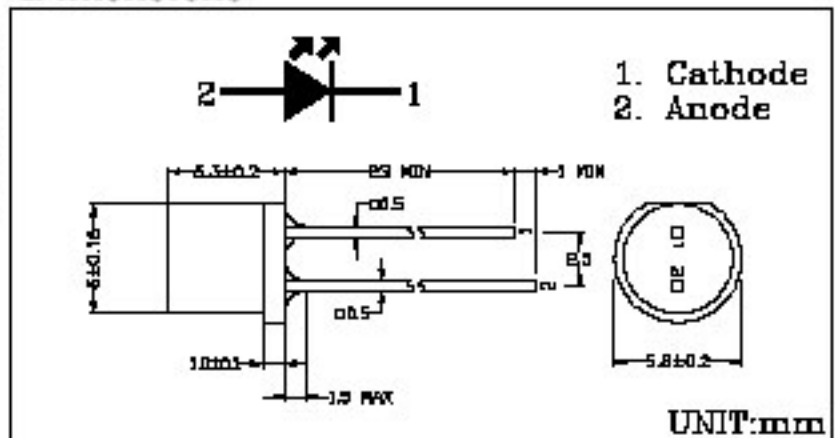
## 1. General Description:

is a high output power GaAlAs infrared light emitting diode, mounted in a clear epoxy end looking cylinder package. It emits narrow band of radiation peaking at 940nm.

## 2. Features

- Extra wide beam angle ( $\pm 70^\circ$ )
- Capable of pulse operation
- High output power
- $\varnothing 5\text{mm}$  cylinder package (Flat-head)
- Low cost

## Dimensions



## 3. Absolute Maximum Ratings

( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Forward Current	$I_F$	100	mA
Pulse Forward current *1	$I_{FP}$	1	A
Reverse Voltage	$V_R$	5	V
Power Dissipation	$P_D$	100	mW
Operating Temperature	$T_{opr}$	-30 ~ +70	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-30 ~ +80	$^\circ\text{C}$
Soldering Temperature *2	$T_{sot}$	260	$^\circ\text{C}$

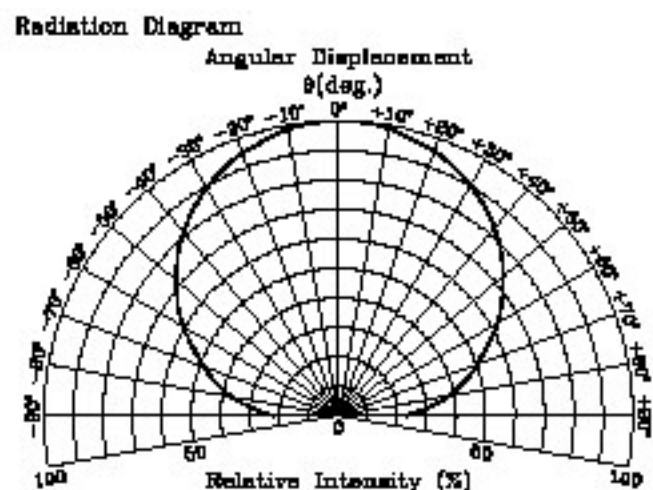
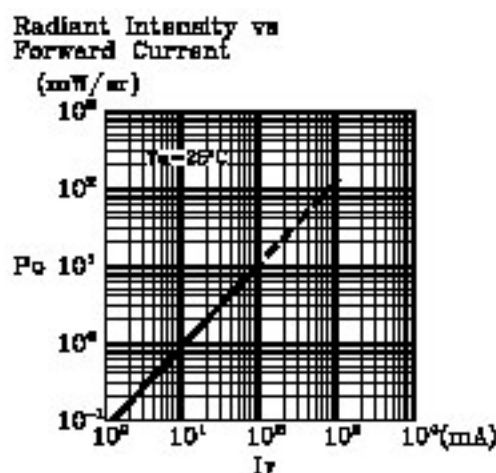
\*1 Pulse width  $\leq 100\mu\text{sec}$ . Time Cycle=10msec.

\*2 At the position of 2mm from the bottom of the package within 5 seconds.

## 4. Electro-optical Characteristics

( $T_a=25^\circ\text{C}$ )

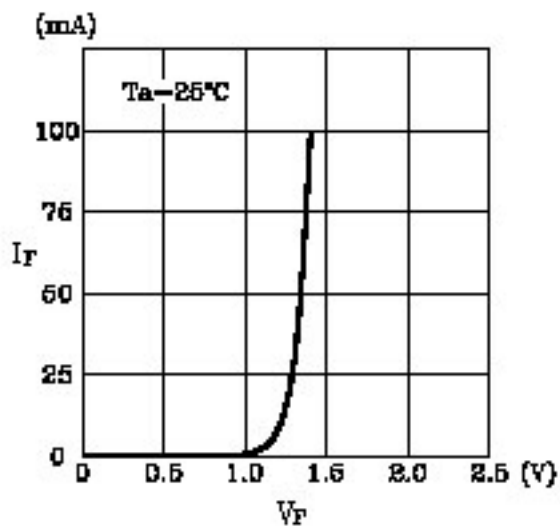
Parameter	Symbol	Testing Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F=100\text{mA}$		1.4	1.7	V
Reverse Current	$I_R$	$V_R=5\text{V}$			10	$\mu\text{A}$
Radiant Intensity	$P_o$	$I_F=100\text{mA}$	4	11		mW/sr
Terminal Capacitance	$C_t$	$f=1\text{MHz}$		40		pF
Half Power Beam Angle	$\Delta\theta$			$\pm 70$		deg.
Peak Emission Wavelength	$\lambda_p$	$I_F=50\text{mA}$		940		nm
Spectral bandwidth at 50%	$\Delta\lambda$	$I_F=50\text{mA}$		45		nm



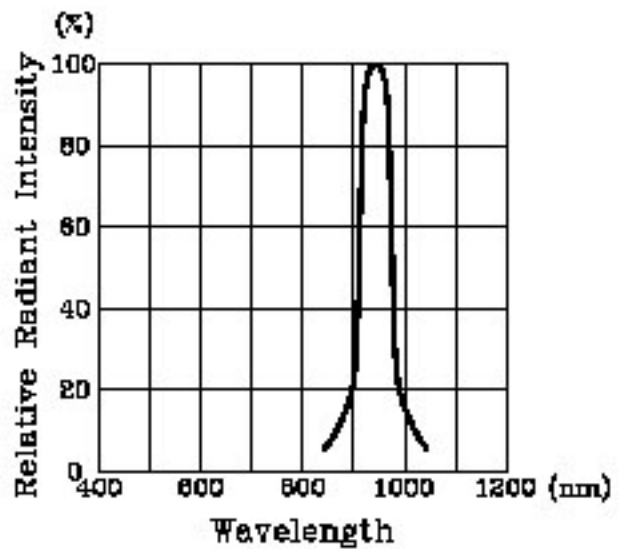
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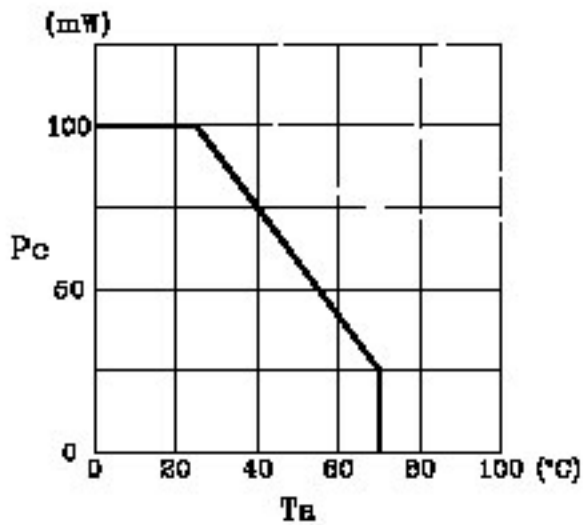
Forward Current vs  
Forward Voltage



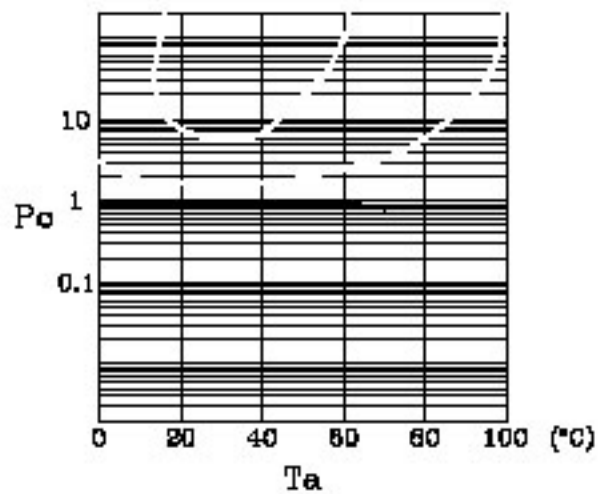
Spectral Distribution



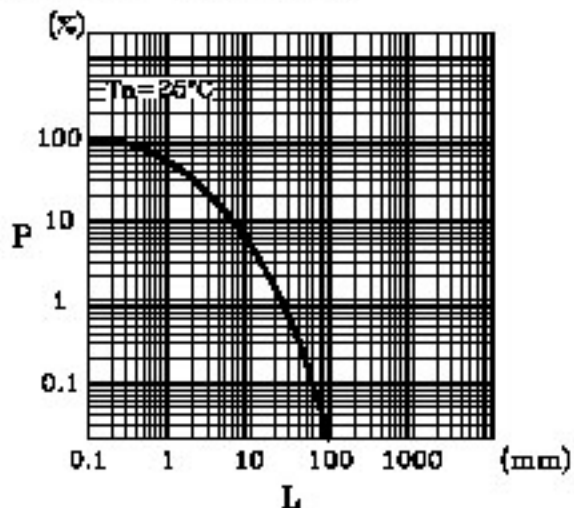
Power Dissipation vs  
Ambient Temperature



Relative Output power vs  
Ambient Temperature



Relative Power vs  
Distance to Detector



Distance to Detector Test Conditions

